[Total Marks: 80]

[3 Hours]

		Attempt any three from the rest.	
		Figure to the right indicates full marks.	
	4.	Assume suitable data if it is necessary.	X.
1			(5 x 4
	a) b)	Explain the need of biasing in BJT amplifiers. Interpret the drain-source characteristics of n-channel depletion type	
		MOSFET for $V_{GS} = 0V$ and $V_{GS} = -2V$.	
	c)	Explain diode as positive shunt clipper.	
	d)	Demonstrate the block diagram of op-amp with the function of each block.	
2	a)	Briefly discuss the different biasing techniques employed in BJT Amplifiers.	(10)
	b)	Draw the hybrid equivalent model of voltage divider bias CE amplifier and derive the expression for voltage gain.	(10)
3	a)	Draw the small signal equivalent circuit of an n-channel MOSFET amplifier derive the expression of voltage gain.	(10)
	b)	Determine the values of I _{DQ} and V _{GSQ} for the Common Source n-channel	
		Depletion type MOSFET in voltage divider bias configuration. $R_{G1} = 91M\Omega$, $R_{G2} = 15M\Omega$, $R_D = 6.8K\Omega$, $R_S = 3.3K\Omega$, $V_{DD} = 18V$, $I_{DSS} = 12mA$, $V_P = -3V$.	(10)
4	a)	Explain op-amp as an inverting amplifier and design an inverting amplifier for voltage gain of -10.	(10)
) ⁷	b)	Explain the working of astable multivibrator using IC 555.	(10)
5	(a)	Explain the construction and working of optoisolators.	(10)
	b)	Explain op-amp as voltage summing amplifier and derive the expression of output voltage.	(10)
_		Write short notes on ANY TWO	(20)
U	(a)	Monostable Multivibrator using IC555	(20)
	b)	Op-amp as Integrator	
	c)	LM317 as Adjustable voltage Regulator	
		20, 100, 100, 100, 100, 100, 100, 100, 1	

Instructions:

1. Question No.1 is compulsory.